

Silicon PNP Power Transistors

BDX66C

DESCRIPTION

- With TO-3 package
- DARLINGTON
- High current

APPLICATIONS

- Designed for power amplification and switching applications.

PINNING (See Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

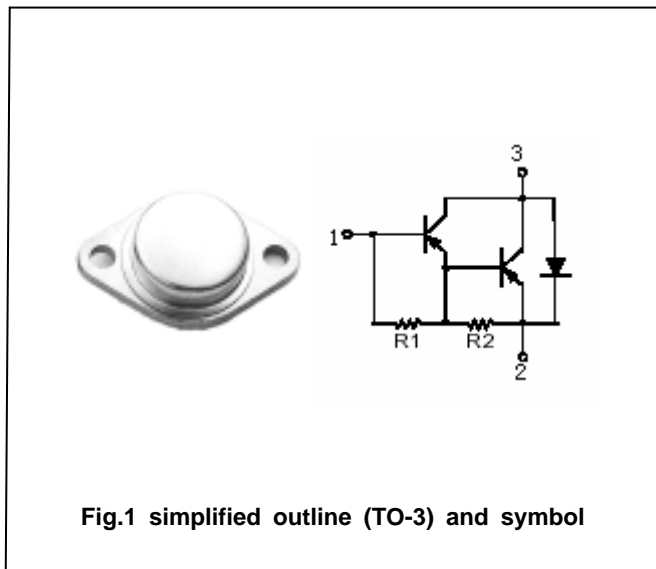


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	-120	V
V _{CEO}	Collector-emitter voltage	Open base	-120	V
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-16	A
I _{CM}	Collector current(peak)		-20	A
I _B	Base current		-0.25	A
P _T	Total power dissipation	T _C =25	150	W
T _j	Junction temperature		-55~200	
T _{stg}	Storage temperature		-55~200	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance from junction to case	1.17	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEQ(SUS)}	Collector-emitter sustaining voltage	I _C =-0.1A ; I _B =0;L=25mH	-120			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =-10A ;I _B =-40mA			-2	V
I _{CBO}	Collector cut-off current	V _{CB} =-70V; I _E =0 T _C =150			-1 -5	mA
I _{CEO}	Collector cut-off current	V _{CE} =-60V; I _B =0			-3	mA
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-5	mA

Switching times

t _{on}	Turn-on time	I _C =-10A ; I _{B1} =-I _{B2} =0.04A V _{CC} =12V ;		1.0		μs
t _{off}	Turn-off time			3.5		μs

PACKAGE OUTLINE

